Title (en)

METHOD FOR DETERMINING A SHEET RESISTANCE OF A SEMICONDUCTOR SUBSTRATE AFTER PLASMA-IMMERSION ION IMPLANTATION AND THERMAL ANNEALING

Title (de)

VERFAHREN ZUR BESTIMMUNG EINES SCHICHTWIDERSTANDES EINES HALBLEITERSUBSTRATS NACH PLASMAIMMERSIONIONENIMPLANTATION UND THERMISCHEM GLÜHEN

Title (fr)

PROCEDE DE DETERMINATION D'UNE RESISTANCE CARREE D'UN SUBSTRAT SEMICONDUCTEUR APRES IMPLANTATION IONIQUE PAR IMMERSION PLASMA ET RECUIT THERMIQUE

Publication

**EP 3888117 A1 20211006 (FR)**

Application

**EP 19806279 A 20191126**

Priority

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- EP 2019082633 W 20191126

Abstract (en)

[origin: WO2020109333A1] One aspect of the invention relates to a method for determining a sheet resistance of a semiconductor substrate after plasma-immersion ion implantation and thermal annealing, by means of a reflectance of the semiconductor substrate after its plasma-immersion ion implantation and before its thermal annealing, and of a lookup table indexing reflectance before thermal annealing and sheet resistance after thermal annealing.

IPC 8 full level

**H01L 21/66** (2006.01); **C23C 14/48** (2006.01); **H01J 37/32** (2006.01); **H01L 31/00** (2006.01)

CPC (source: EP)

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Citation (search report)

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**FR 3089014 A1 20200529**; **FR 3089014 B1 20220805**; EP 3888117 A1 20211006; JP 2022511762 A 20220201; WO 2020109333 A1 20200604

DOCDB simple family (application)

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